

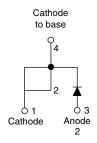
www.vishay.com

Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 25 A



TO-247AC modified



PRODUCT SUMMARY	
Package	TO-247AC modified (2 pins)
I _{F(AV)}	25 A
V _R	600 V
V _F at I _F	1.7 V
t _{rr} (yp.	23 ns
T _J max.	150 °C
Diode variation	Single die

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC-JESD47
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA25PB60... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the VS-HFA25PB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA25PB60... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V_{R}		600	V					
Maximum continuous forward current	I _F	T _C = 100 °C	25						
Single pulse forward current	I _{FSM}		225	Α					
Maximum repetitive forward current	I _{FRM}		100						
Maximum power dissipation	D	T _C = 25 °C	151	W					
Maximum power dissipation	P_{D}	T _C = 100 °C	60]					
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C					



VS-HFA25PB60PbF, VS-HFA25PB60-N3

Vishay Semiconductors

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		600	-	-			
Maximum forward voltage		I _F = 25 A		-	1.3	1.7	V		
	V_{FM}	I _F = 50 A	See fig. 1	-	1.5	2.0			
		I _F = 25 A, T _J = 125 °C		-	1.3	1.7			
Maximum reverse ,		V _R = V _R rated	See fig. 2	-	1.5	20			
leakage current	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	See lig. 2	-	600	2000	μΑ		
Junction capacitance	C _T	V _R = 200 V See fig		-	55	100	pF		
Series inductance	L _S	Measured lead to lead 5 mm from body	-	12	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	0 A/μs, V _R = 30 V	-	23	-	ns		
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	50	75			
oee lig. 5, 10	t _{rr2}	T _J = 125 °C	$I_F = 25 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	105	160			
Peak recovery current See fig. 6, 10	I _{RRM1}	T _J = 25 °C		-	4.5	10	A nC		
	I _{RRM2}	T _J = 125 °C		-	8.0	15			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	112	375			
See fig. 7, 10	Q _{rr2}	T _J = 125 °C		-	420	1200	110		
Peak rate of fall of recovery current during t _b See fig. 8, 10	dl _{(rec)M} /dt1	T _J = 25 °C		-	250	-	Λ/μς		
	dI _{(rec)M} /dt2	T _J = 125 °C		-	160	-	- A/μs		

THERMAL - MECHA	THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS					
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C					
Thermal resistance, junction to case	R _{thJC}		-	-	0.83						
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W					
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-						
Weight			-	6.0	-	g					
vveigni			-	0.21	-	oz.					
Mounting torque			6.0 (5.0)	-	12 (10)	kgf ·cm (lbf ·in)					
Marking device		Case style TO-247AC modified (JEDEC)	HFA25PB60								



www.vishay.com

Vishay Semiconductors

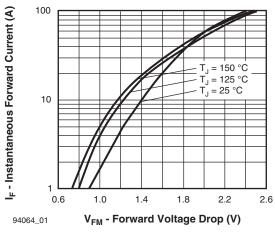


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

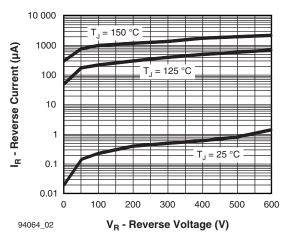


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

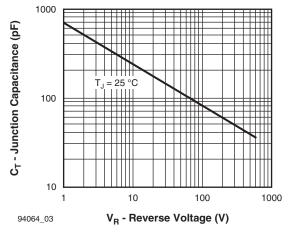


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

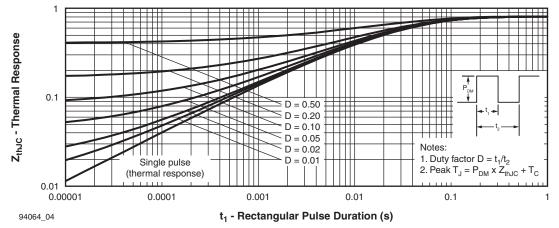


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

www.vishay.com

Vishay Semiconductors

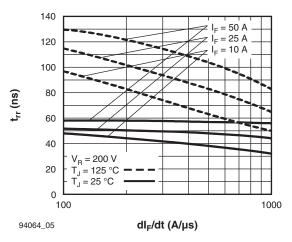


Fig. 5 - Typical Reverse Recovery Time vs. dl_E/dt

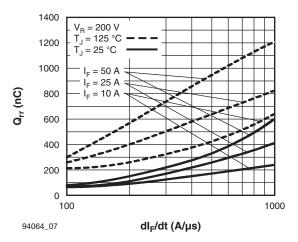


Fig. 7 - Typical Stored Charge vs. dl_F/dt

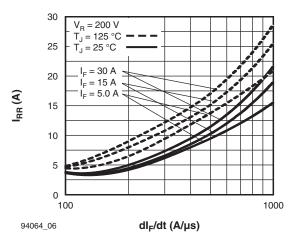


Fig. 6 - Typical Recovery Current vs. dl_F/dt

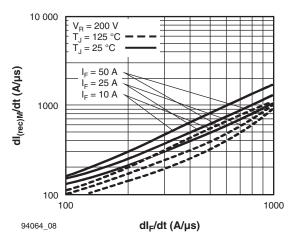


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

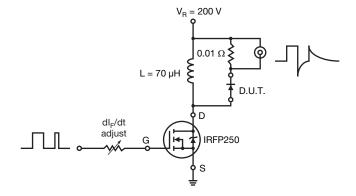
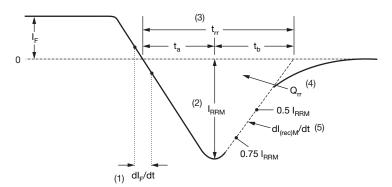


Fig. 9 - Reverse Recovery Parameter Test Circuit

VS-HFA25PB60PbF, VS-HFA25PB60-N3

Vishay Semiconductors

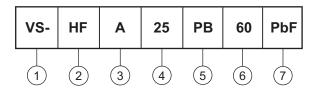


- (1) dl_F/dt rate of change of current through zero crossing
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_{F}$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (5) dI_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 HEXFRED® family
- 3 Electron irradiated
- 4 Current rating (25 = 25 A)
- PB = TO-247AC modified
- 6 Voltage rating: (60 = 600 V)
- 7 Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA25PB60PbF	25	500	Antistatic plastic tube						
VS-HFA25PB60-N3	25	500	Antistatic plastic tube						

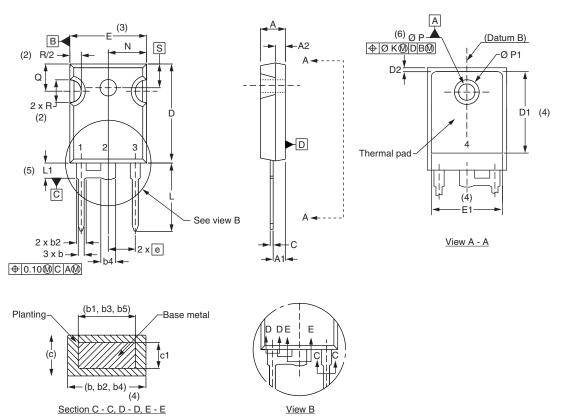
LINKS TO RELATED DOCUMENTS								
Dimensions		www.vishay.com/doc?95541						
Part marking information	TO-247AC modified PbF	www.vishay.com/doc?95255						
	TO-247AC modified -N3	www.vishay.com/doc?95442						



Vishay Semiconductors

TO-247 modified

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	MILLIMETERS INCHES		ICHES		INCHES		NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		
Α	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053			
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3		
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-			
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC			
b1	0.99	1.35	0.039	0.053			ØK	0.2	254	0.0	010			
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634			
b3	1.65	2.33	0.065	0.092			L1	3.71	4.29	0.146	0.169			
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0	.3			
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.144			
С	0.38	0.89	0.015	0.035			Ø P1	-	7.39	-	0.291			
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224			
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216			
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	' BSC			

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000